

NTH4L018N075SC1

Silicon Carbide (SiC) MOSFET, N-Channel - EliteSiC, 13.5mohm, 750V, M2, TO247-4L

Product Overview

For complete documentation, see the data sheet.

EliteSiC MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

- TJ = 175°C
- Ultra Low Gate Charge (Typ. Qg = 262 nC)
- High Speed Switching with Low Capacitance (Coss = 365 pF)
- Zero reverse recovery current of body diode
- Kelvin Source configuration
- Typ. RDS(on) = 13.5 m at Vgs = 18V
- 100% UIL Tested
- RoHS Compliant


Applications

- Industrial

End Products

- UPS / ESS
- Solar
- EV Charger

Part Electrical Specifications

Product	Status	Compliance	Famil y	Block ing Volta ge BV <sub>DS</sub> (V)	I <sub>D(max)</sub> (A)	R <sub>DS(on)</sub> Typ ) @ 25°C (mΩ)	Q <sub>g</sub> Total (nC)	Outp ut Capa citan ce (pF)	T <sub>j</sub> Max (°C)	Pack age Type	Case Outli ne	MSL Type	MSL Tem p (°C)	Cont ainer Type	Cont ainer Qty.
NTH4L018N075 SC1	Active		M2	750	140	13.5	262	365	175	TO- 247- 4	340 C.J.P DF	1	245	TUB E	450